



P-CHANNEL ENHANCEMENT MODE MOSFET

Features

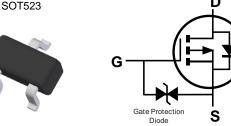
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **ESD Protected Gate**
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

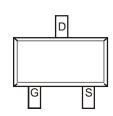
Mechanical Data

- Case: SOT523
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Alloy 42 leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Terminal Connections: See Diagram
- Weight: 0.002 grams (Approximate)









Top View

Equivalent Circuit

Top View

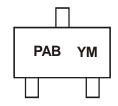
Ordering Information (Note 4)

Part Number	Case	Packaging
DMP2004TK-7	SOT523	3,000/Tape & Reel

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. Notes:

- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + CI) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



PAB = Product Type Marking Code YM = Date Code Marking Y = Year (ex: F = 2018)M = Month (ex: 9 = September)

Date Code Key

Year	2006	2007		2014	2015	2016	2017	2018	2019	2020	2021	2022
Code	Т	U		В	С	D	Е	F	G	Н	I	J
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code		^	2	4	r .	^	7	0		^	N	_

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Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Chara	acteristic		Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	-20	V
Gate-Source Voltage			V _{GSS}	±8	V
Drain Current (Note 5)	Steady State	$T_A = +25$ °C $T_A = +85$ °C	I _D	-430 -310	mA
Pulsed Drain Current (Note 6)			I _{DM}	-750	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		P_{D}	230	mW
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	558	°C/W
Total Power Dissipation (Note 6)		P_{D}	320	mW
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{θJA}	393	°C/W
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

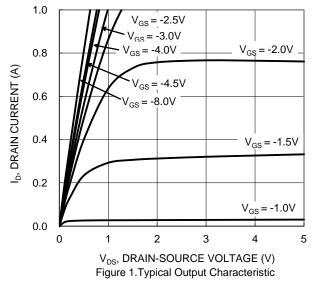
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
OFF CHARACTERISTICS (Note 7)								
Drain-Source Breakdown Voltage	BV _{DSS}	-20	_		V	$V_{GS} = 0V, I_D = -250\mu A$		
Zero Gate Voltage Drain Current	I _{DSS}	_	_	-1.0	μΑ	V _{DS} = -20V, V _{GS} = 0V		
Gate-Source Leakage	I _{GSS}	_	_	±1.0	μΑ	$V_{GS} = \pm 4.5V, V_{DS} = 0V$		
ON CHARACTERISTICS (Note 7)								
Gate Threshold Voltage	V _{GS(TH)}	-0.5	_	-1.0	V	$V_{DS} = V_{GS}, I_D = -250 \mu A$		
			0.7	1.1		$V_{GS} = -4.5V$, $I_D = -430mA$		
Static Drain-Source On-Resistance	R _{DS(ON)}	_	1.0	1.6	Ω	$V_{GS} = -2.5V, I_D = -300mA$		
			1.3	2.4		$V_{GS} = -1.8V, I_D = -150mA$		
Diode Forward Voltage	V_{SD}	_	-0.8	-1.4	V	$V_{GS} = 0V, I_{S} = -115mA$		
DYNAMIC CHARACTERISTICS (Note 8)								
Input Capacitance	C _{iss}	_	47		pF	V _{DS} = -16V, V _{GS} = 0V f = 1.0MHz		
Output Capacitance	Coss		6.8	_	pF			
Reverse Transfer Capacitance	C _{rss}	1	4.9	_	pF	1 = 1:0WI 12		
Gate Resistance	R_{g}		240	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$		
Total Gate Charge V _{GS} = -4.5V	Q_{g}	1	0.55	_	nC			
Total Gate Charge V _{GS} = -8V	Qg	1	0.97	_	nC	$V_{DS} = -10V, I_{D} = -250mA$		
Gate-Source Charge	Q_{gs}		0.05	_	nC			
Gate-Drain Charge	Q_{gd}	_	0.1	_	nC			
Turn-On Delay Time	t _{D(ON)}	_	5.9	_	ns			
Turn-On Rise Time	t _R	_	3.3	_	ns	$V_{DD} = -3V, V_{GS} = -2.5V,$		
Turn-Off Delay Time	t _{D(OFF)}	_	25.5	_	ns	$R_G = 25\Omega$, $I_D = -100 \text{mA}$		
Turn-Off Fall Time	t _F	_	19.3	_	ns			
Reverse Recovery Time	t _{RR}		7.3	_	ns	I _F =-1A, di/dt=-100A/μs		
Reverse Recovery Charge	Q_{RR}		1.9	_	nC	I _F =-1A, di/dt=-100A/μs		

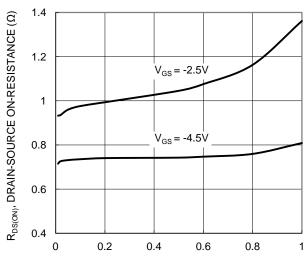
5. Device mounted on FR-4 PCB, with minimum recommended pad layout.

- 6. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
- 7. Short duration pulse test used to minimize self-heating effect.
 8. Guaranteed by design. Not subject to product testing.

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I_D, DRAIN-SOURCE CURRENT (A) Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

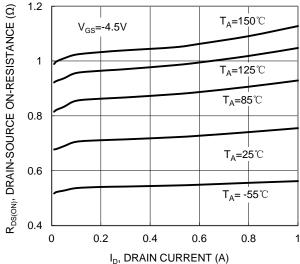


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

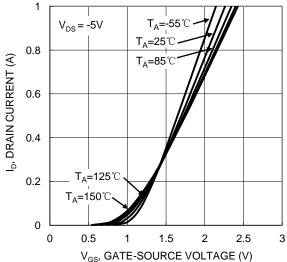
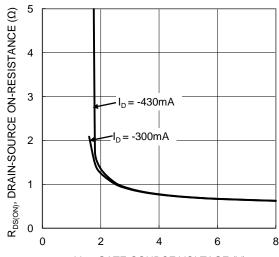


Figure 2. Typical Transfer Characteristic



V_{GS}, GATE-SOURCE VOLTAGE (V) Figure 4. Typical Transfer Characteristic

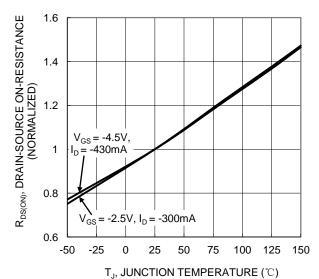
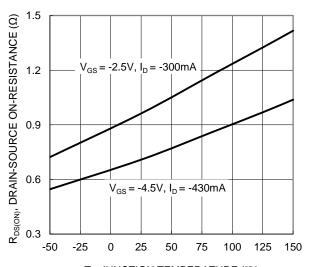
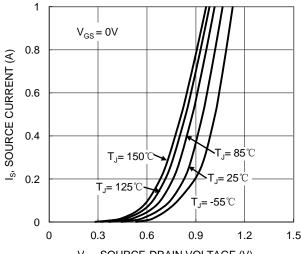


Figure 6. On-Resistance Variation with Temperature

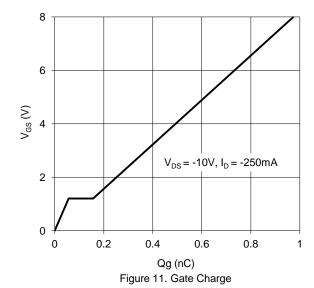


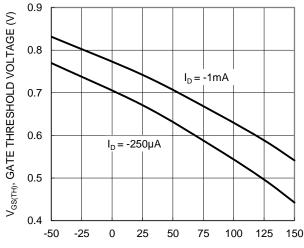


T_J, JUNCTION TEMPERATURE (℃) Figure 7. On-Resistance Variation with Temperature

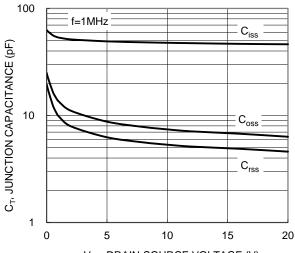


V_{SD}, SOURCE-DRAIN VOLTAGE (V) Figure 9. Diode Forward Voltage vs. Current

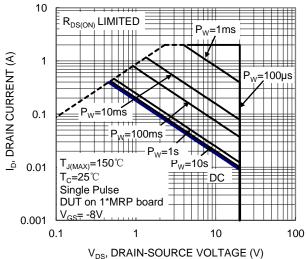




 T_J , JUNCTION TEMPERATURE (°C) Figure 8. Gate Threshold Variation vs. JunctionTemperature



V_{DS}, DRAIN-SOURCE VOLTAGE (V) Figure 10. Typical Junction Capacitance



V_{DS}, DRAIN-SOURCE VOLTAGE (V) Figure 12. SOA, Safe Operation Area



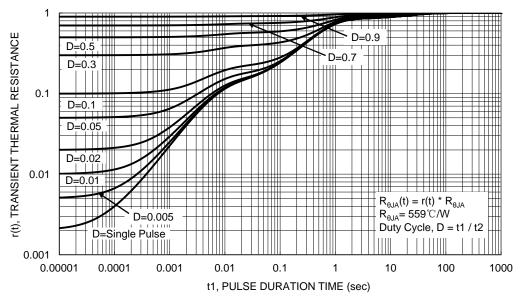
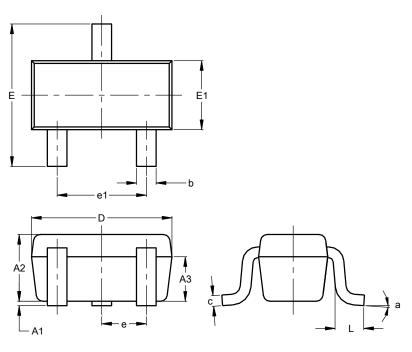


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT523



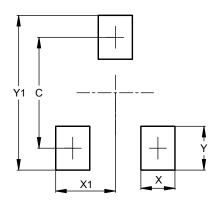
SOT523							
Dim	Min	Max	Тур				
A1	0.00	0.10	0.05				
A2	0.60	0.80	0.75				
A3	0.45	0.65	0.50				
b	0.15	0.30	0.22				
С	0.10	0.20	0.12				
D	1.50	1.70	1.60				
E	1.45	1.75	1.60				
E1	0.75	0.85	0.80				
е	0.50 BSC						
e1	0.90	1.10	1.00				
L	0.20	0.40	0.33				
а	0°		8°				
All Dimensions in mm							



Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT523



Dimensions	Value (in mm)
С	1.29
Х	0.40
X1	0.70
Y	0.51
Y1	1.80

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